

**AMENDMENTS TO THE CLAIMS:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

**LISTING OF CLAIMS:**

1. - 21. (Cancelled)

22. (Currently Amended) A capacitor of a semiconductor device, the capacitor comprising:

a lower electrode;

an AHO( $(\text{Al}_x\text{Hf}_{1-x})\text{O}_y$ ) film formed on the lower electrode;

an upper electrode formed on the AHO film; and

a dielectric film having a dielectric constant that is higher than that of the AHO film between the upper electrode and the AHO layer,

wherein the dielectric film is an  $\text{HfO}_2$  layer, a  $\text{ZrO}_2$  layer, or an STO layer.

23. (Original) The capacitor of claim 22, further comprising an oxidation barrier film formed between the lower electrode and the AHO layer.

24. - 37. (Cancelled)